



**THE DATASHEET OF
NGTB45N60S1WG**



NGTB45N60S1WG

IGBT - Inverter Welding

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Trench construction, and provides superior performance in demanding switching applications, offering both low on state voltage and minimal switching loss. The IGBT is well suited for welding applications. Incorporated into the device is a soft and fast co-packaged free wheeling diode with a low forward voltage.

Features

- $T_{Jmax} = 175^{\circ}C$
- Soft Fast Reverse Recovery Diode
- Optimized for High Speed Switching
- 5 μs Short-Circuit Capability
- These are Pb-Free Devices

Typical Applications

- Welding

ABSOLUTE MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-emitter voltage	V_{CES}	600	V
Collector current @ $T_c = 25^{\circ}C$ @ $T_c = 100^{\circ}C$	I_c	90 45	A
Diode Forward Current @ $T_c = 25^{\circ}C$ @ $T_c = 100^{\circ}C$	I_F	90 45	A
Diode Pulsed Current T_{PULSE} Limited by T_J Max	I_{FM}	180	A
Pulsed collector current, T_{pulse} limited by T_{Jmax}	I_{CM}	180	A
Short-circuit withstand time $V_{GE} = 15 V$, $V_{CE} = 400 V$, $T_J \leq +150^{\circ}C$	t_{SC}	5	μs
Gate-emitter voltage	V_{GE}	± 20	V
Transient gate-emitter voltage ($T_{PULSE} = 5 \mu s$, $D < 0.10$)		± 30	V
Power Dissipation @ $T_c = 25^{\circ}C$ @ $T_c = 100^{\circ}C$	P_D	300 150	W
Operating junction temperature range	T_J	-55 to +175	$^{\circ}C$
Storage temperature range	T_{stg}	-55 to +175	$^{\circ}C$
Lead temperature for soldering, 1/8" from case for 5 seconds	T_{SLD}	260	$^{\circ}C$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



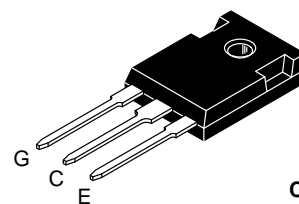
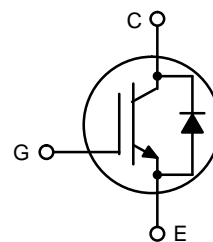
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45 A, 600 V

$V_{CEsat} = 2.00 V$

$E_{OFF} = 0.53 mJ$



**TO-247
CASE 340AL**

MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- WW = Work Week
- G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
NGTB45N60S1WG	TO-247 (Pb-Free)	30 Units / Rail

NGTB45N60S1WG

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction-to-case, for IGBT	$R_{\theta JC}$	0.50	°C/W
Thermal resistance junction-to-case, for Diode	$R_{\theta JC}$	1.00	°C/W
Thermal resistance junction-to-ambient	$R_{\theta JA}$	40	°C/W

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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STATIC CHARACTERISTIC

Collector-emitter breakdown voltage, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, I_C = 500\ \mu\text{A}$	$V_{(BR)CES}$	600	–	–	V
Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 45\text{ A}$ $V_{GE} = 15\text{ V}, I_C = 45\text{ A}, T_J = 175^\circ\text{C}$	V_{CEsat}	1.50 –	2.00 2.60	2.40 –	V
Gate-emitter threshold voltage	$V_{GE} = V_{CE}, I_C = 350\ \mu\text{A}$	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector-emitter cut-off current, gate-emitter short-circuited	$V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}$ $V_{GE} = 0\text{ V}, V_{CE} = 600\text{ V}, T_J = 175^\circ\text{C}$	I_{CES}	–	–	0.5 4.0	mA
Gate leakage current, collector-emitter short-circuited	$V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$	I_{GES}	–	–	200	nA

DYNAMIC CHARACTERISTIC

Input capacitance	$V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$	C_{ies}	–	3115	–	pF
Output capacitance		C_{oes}	–	149	–	
Reverse transfer capacitance		C_{res}	–	88	–	
Gate charge total	$V_{CE} = 480\text{ V}, I_C = 45\text{ A}, V_{GE} = 15\text{ V}$	Q_g	–	125	–	nC
Gate to emitter charge		Q_{ge}	–	32	–	
Gate to collector charge		Q_{gc}	–	65	–	

SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

Turn-on delay time	$T_J = 25^\circ\text{C}$ $V_{CC} = 400\text{ V}, I_C = 45\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	$t_{d(on)}$	–	72	–	ns	
Rise time		t_r	–	33	–		
Turn-off delay time		$t_{d(off)}$	–	132	–		
Fall time		$T_J = 150^\circ\text{C}$ $V_{CC} = 400\text{ V}, I_C = 45\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	t_f	–	68	–	mJ
Turn-on switching loss			E_{on}	–	1.25	–	
Turn-off switching loss			E_{off}	–	0.53	–	
Total switching loss			E_{ts}	–	1.78	–	
Turn-on delay time	$T_J = 150^\circ\text{C}$ $V_{CC} = 400\text{ V}, I_C = 45\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	$t_{d(on)}$	–	70	–	ns	
Rise time		t_r	–	38	–		
Turn-off delay time		$t_{d(off)}$	–	135	–		
Fall time		$T_J = 150^\circ\text{C}$ $V_{CC} = 400\text{ V}, I_C = 45\text{ A}$ $R_g = 10\ \Omega$ $V_{GE} = 0\text{ V}/15\text{ V}$	t_f	–	88	–	mJ
Turn-on switching loss			E_{on}	–	1.59	–	
Turn-off switching loss			E_{off}	–	0.88	–	
Total switching loss			E_{ts}	–	2.47	–	

DIODE CHARACTERISTIC

Forward voltage	$V_{GE} = 0\text{ V}, I_F = 45\text{ A}$ $V_{GE} = 0\text{ V}, I_F = 45\text{ A}, T_J = 175^\circ\text{C}$	V_F	1.50 –	2.45 2.62	2.90 –	V
Reverse recovery time	$T_J = 25^\circ\text{C}$ $I_F = 45\text{ A}, V_R = 200\text{ V}$ $di_F/dt = 200\text{ A}/\mu\text{s}$	t_{rr}	–	70	–	ns
Reverse recovery charge		Q_{rr}	–	272	–	nC
Reverse recovery current		I_{rrm}	–	7	–	A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

NGTB45N60S1WG

TYPICAL CHARACTERISTICS

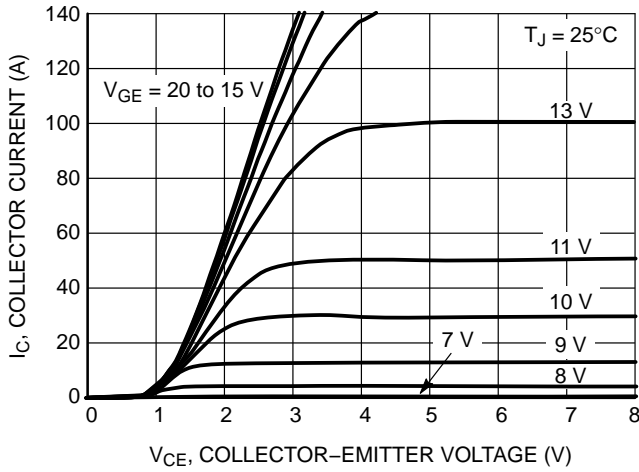


Figure 1. Output Characteristics

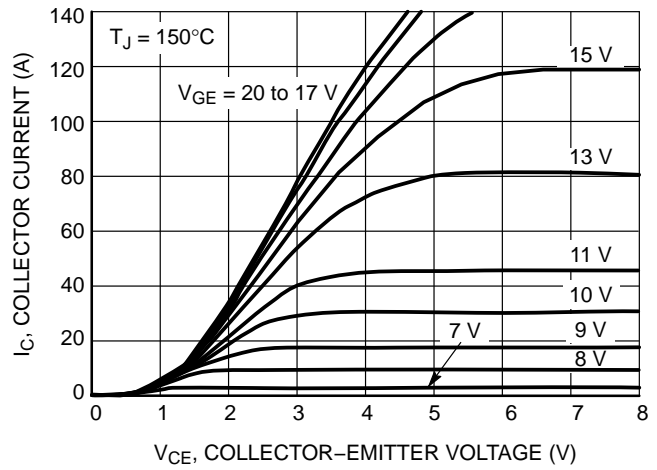


Figure 2. Output Characteristics

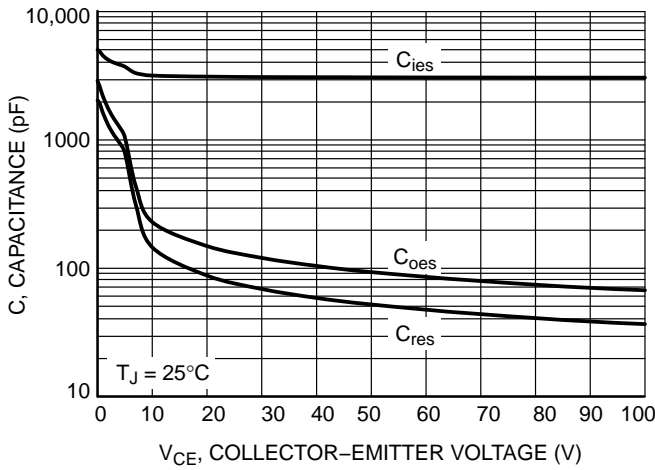


Figure 3. Typical Capacitance

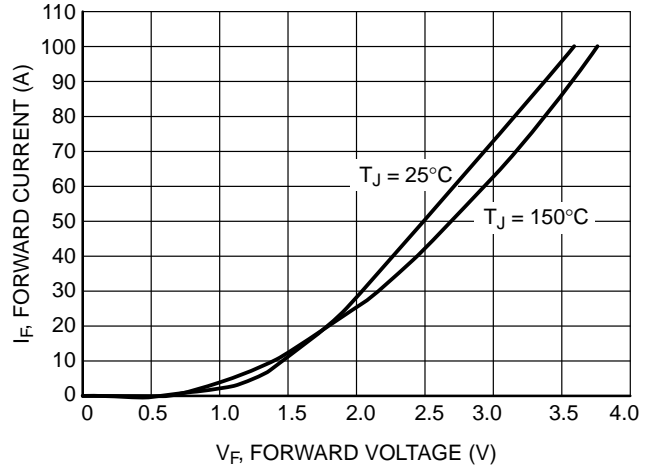


Figure 4. Diode Forward Characteristics

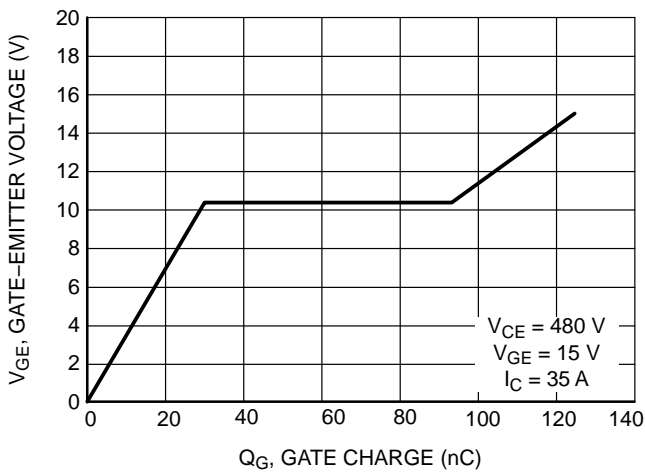


Figure 5. Typical Gate Charge

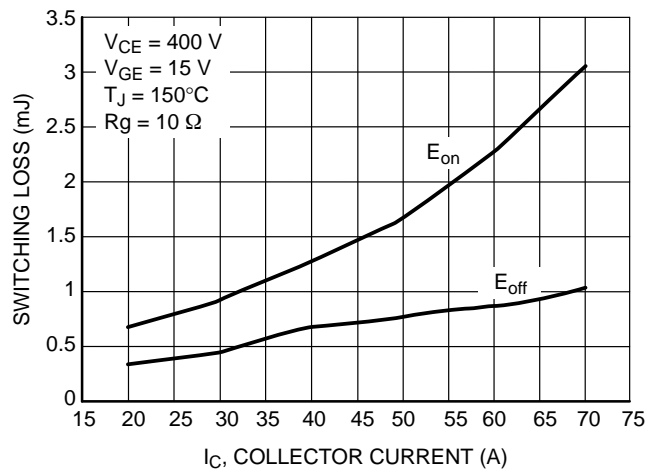


Figure 6. Switching Loss vs. I_c

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TYPICAL CHARACTERISTICS

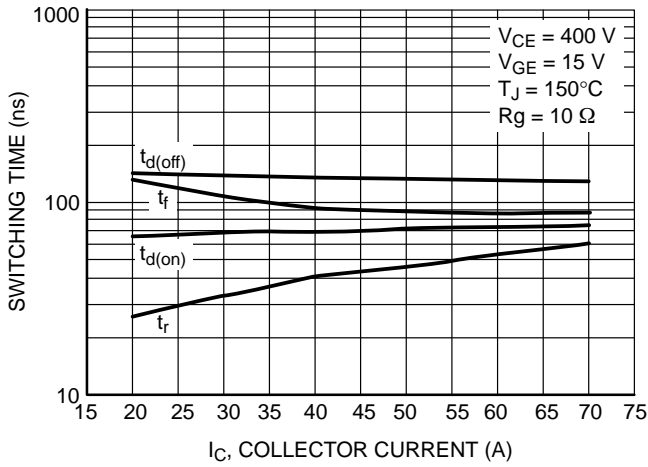


Figure 7. Switching Time vs. I_C

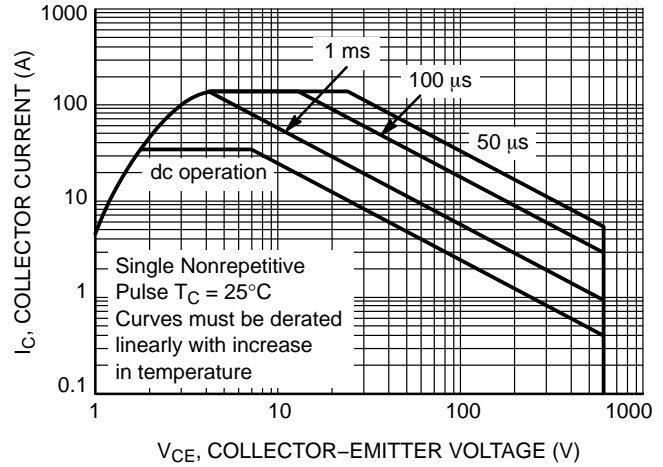


Figure 8. Safe Operating Area

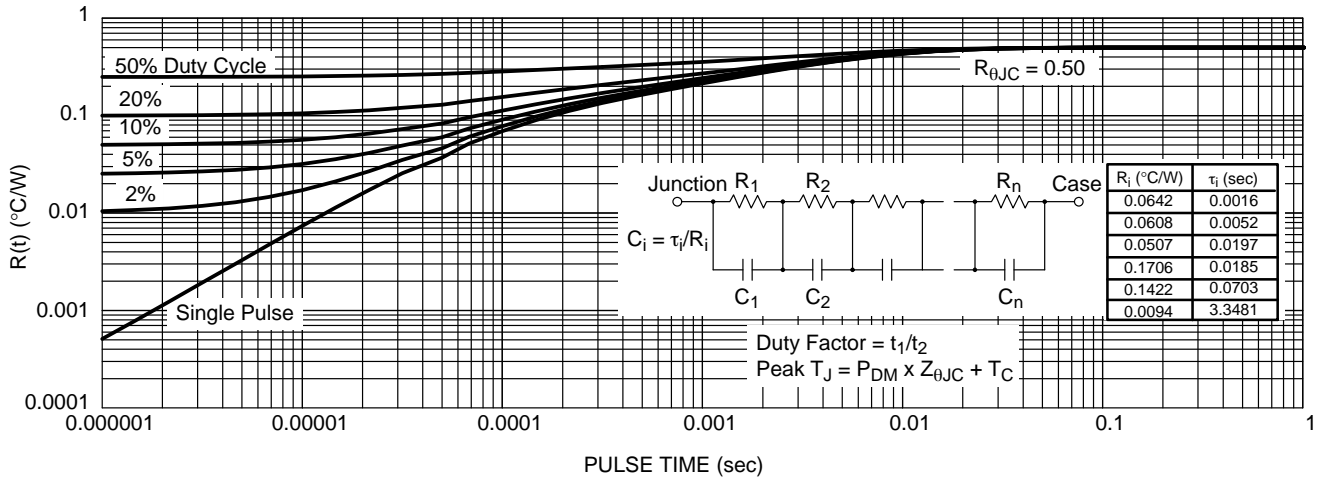


Figure 9. IGBT Transient Thermal Impedance

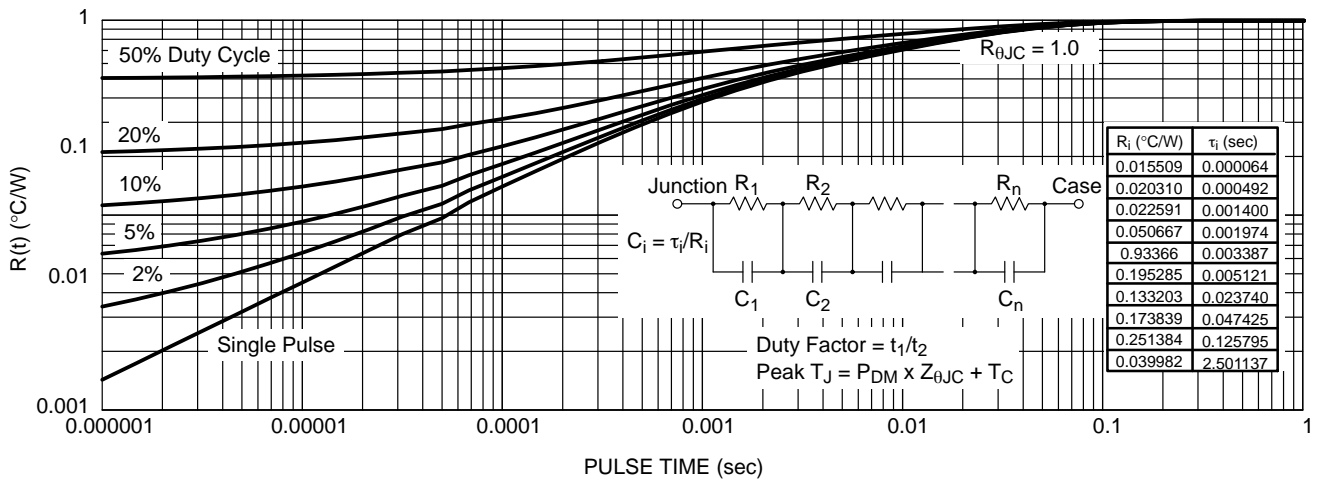


Figure 10. Diode Transient Thermal Impedance

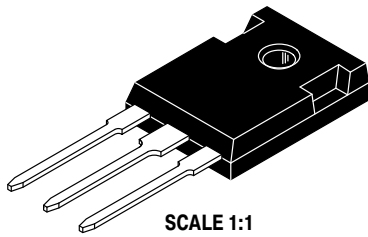
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

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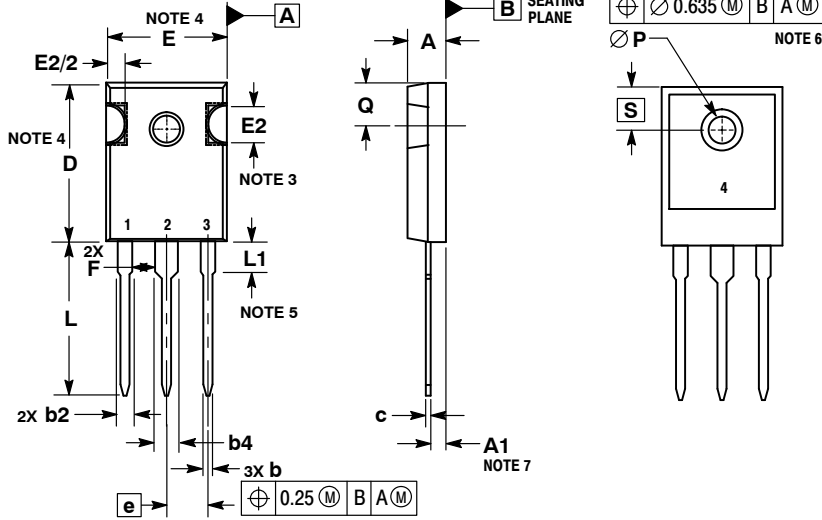


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DATE 17 MAR 2017



SCALE 1:1

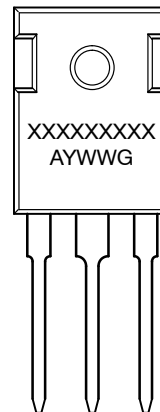


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
5. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.
6. ØP SHALL HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM DIAMETER OF 3.91.
7. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.

MILLIMETERS		
DIM	MIN	MAX
A	4.70	5.30
A1	2.20	2.60
b	1.07	1.33
b2	1.65	2.35
b4	2.60	3.40
c	0.45	0.68
D	20.80	21.34
E	15.50	16.25
E2	4.32	5.49
e	5.45 BSC	
F	2.655	---
L	19.80	20.80
L1	3.81	4.32
P	3.55	3.65
Q	5.40	6.20
S	6.15 BSC	

GENERIC MARKING DIAGRAM*



- XXXXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- WW = Work Week
- G = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "▪", may or may not be present.

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